BC337, BC337-25, BC337-40

Amplifier Transistors

NPN Silicon

Features

• These are Pb-Free Devices

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	45	Vdc
Collector - Base Voltage	V _{CBO}	50	Vdc
Emitter – Base Voltage	V _{EBO}	5.0	Vdc
Collector Current - Continuous	Ic	800	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

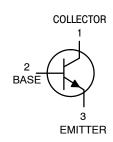
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

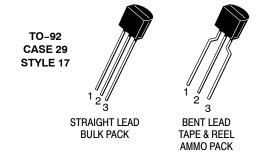
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



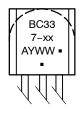
ON Semiconductor®

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MARKING DIAGRAM



BC337-xx = Device Code

(Refer to page 4)

A = Assembly Location

Y = Year
WW = Work Week
Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	·				
Collector – Emitter Breakdown Voltage ($I_C = 10 \text{ mA}, I_B = 0$)	V _{(BR)CEO}	45	-	-	Vdc
Collector – Emitter Breakdown Voltage (I_C = 100 μ A, I_E = 0)	V _{(BR)CES}	50	-	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = 10 \ \mu A, \ I_C = 0$)	V _{(BR)EBO}	5.0	-	-	Vdc
Collector Cutoff Current (V _{CB} = 30 V, I _E = 0)	I _{CBO}	-	-	100	nAdc
Collector Cutoff Current (V _{CE} = 45 V, V _{BE} = 0)	I _{CES}	-	-	100	nAdc
Emitter Cutoff Current (V _{EB} = 4.0 V, I _C = 0)	I _{EBO}	-	-	100	nAdc
ON CHARACTERISTICS	·				
BC3	h _{FE} BC337 37-25 37-40	100 160 250 60	- - - -	630 400 630	-
Base–Emitter On Voltage (I _C = 300 mA, V _{CE} = 1.0 V)	V _{BE(on)}	-	-	1.2	Vdc
Collector – Emitter Saturation Voltage (I _C = 500 mA, I _B = 50 mA)	V _{CE(sat)}	-	-	0.7	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Output Capacitance (V _{CB} = 10 V, I _E = 0, f = 1.0 MHz)	C _{ob}	-	15	-	pF
Current – Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 V, f = 100 MHz)	f _T	-	210	-	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

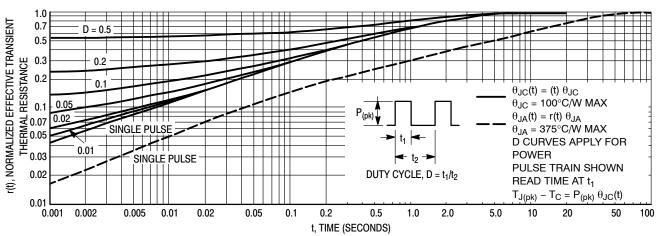


Figure 1. Thermal Response

BC337, BC337-25, BC337-40

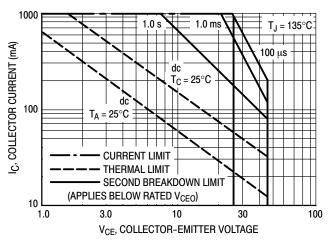


Figure 2. Active Region - Safe Operating Area

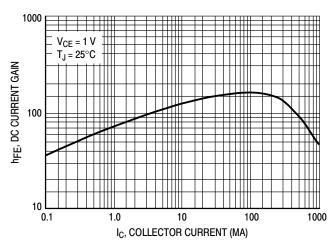


Figure 3. DC Current Gain

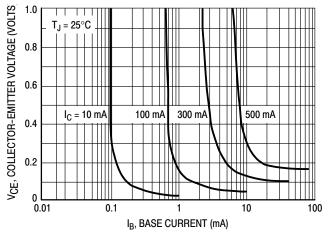


Figure 4. Saturation Region

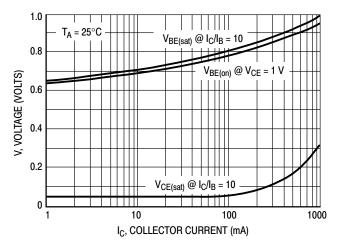


Figure 5. "On" Voltages

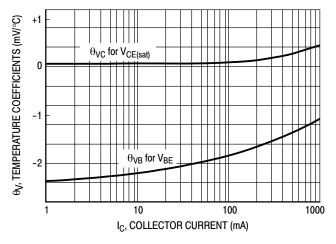


Figure 6. Temperature Coefficients

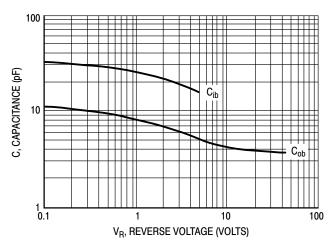


Figure 7. Capacitances

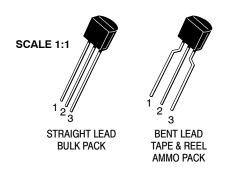
BC337, BC337-25, BC337-40

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
BC337G	7		5000 Units / Bulk
BC337RL1G	7		2000 / Tape & Reel
BC337-025G	7–25		5000 Units / Bulk
BC337-25RL1G	7–25	TO-92 (Pb-Free)	2000 / Tape & Reel
BC337-25RLRAG	7–25		2000 / Tape & Reel
BC337-25ZL1G	7–25		2000 / Ammo Box
BC337-040G	7–40		5000 Units / Bulk
BC337-40RL1G	7–40		2000 / Tape & Reel
BC337-40ZL1G	7–40		2000 / Ammo Box

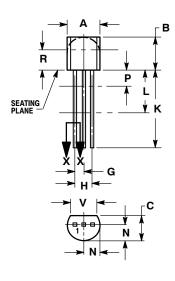
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





TO-92 (TO-226) CASE 29-11 **ISSUE AM**

DATE 09 MAR 2007

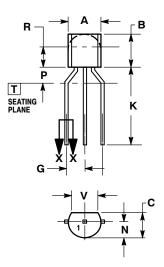


STRAIGHT LEAD **BULK PACK**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
7	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS				
DIM	MIN	MAX			
Α	4.45	5.20			
В	4.32	5.33			
С	3.18	4.19			
D	0.40	0.54			
G	2.40	2.80			
J	0.39	0.50			
K	12.70				
N	2.04	2.66			
P	1.50	4.00			
R	2.93				
V	3.43				

STYLES ON PAGE 2

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TO-92 (TO-226) CASE 29-11

ISSUE AM

DATE 09 MAR 2007

STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	STYLE 4: PIN 1. 2. 3.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	DRAIN SOURCE GATE
STYLE 6: PIN 1. 2. 3.	GATE SOURCE & SUBSTRATE DRAIN	STYLE 7: PIN 1. 2. 3.	SOURCE DRAIN GATE	STYLE 8: PIN 1. 2. 3.	DRAIN GATE SOURCE & SUBSTRATE	STYLE 9: PIN 1. 2. 3.	BASE 1 EMITTER BASE 2	STYLE 10: PIN 1. 2. 3.	CATHODE GATE
STYLE 11: PIN 1. 2. 3.	ANODE CATHODE & ANODE CATHODE	STYLE 12: PIN 1. 2. 3.	MAIN TERMINAL 1 GATE MAIN TERMINAL 2	STYLE 13: PIN 1. 2. 3.	ANODE 1 GATE CATHODE 2	STYLE 14: PIN 1. 2. 3.	EMITTER COLLECTOR BASE	PIN 1. 2.	
2.	ANODE GATE CATHODE	2.	BASE	2.	ANODE CATHODE NOT CONNECTED	2.	ANODE	2.	NOT CONNECTED
PIN 1. 2.	COLLECTOR	PIN 1. 2.	SOURCE GATE DRAIN	STYLE 23: PIN 1. 2. 3.	GATE SOURCE DRAIN	STYLE 24: PIN 1. 2. 3.	EMITTER COLLECTOR/ANODE CATHODE		MT 1 GATE
		2.	MT SUBSTRATE MT	2.		PIN 1. 2.	ANODE	STYLE 30: PIN 1. 2. 3.	DRAIN GATE
	GATE	PIN 1. 2.	BASE COLLECTOR EMITTER	STYLE 33: PIN 1. 2. 3.	RETURN	2.			

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98ASB42022	В

PAGE 3 OF 3

ISSUE	REVISION	DATE
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